

CLAIMS:

1. Detection circuit for detecting the output power of a power amplifier,
comprising:
 - a first current mirror transistor (T11) having a base, which is connectable to a power transistor (T10), and a collector;
 - 5 - a RF detection means (RF-det) for detecting the RF current flowing through the current mirror transistor (T11), wherein said RF detection means (RF-det) is connected to the collector of said first current mirror transistor (T11), and
 - a biasing means (bias-RF-det) for biasing said RF detection means (RF-det), wherein said biasing means is connected to said collector of said first current mirror (T11)
 - 10 and said RF detection means (RF-det).
2. Detection circuit according to claim 1, further comprising a DC detector (DC-det) for detecting the DC components of the current flowing through said first current mirror transistor (T11), wherein said DC detector (DC-det) is connected to said collector of said first
15 current mirror transistor (T11).
3. Detection circuit according to claim 1, further comprising:
 - a second current mirror transistor (T12) having a base which is connectable to a power transistor (T10), and
 - 20 - a DC detector (DC-det) for detecting the DC components of the current flowing through said second current mirror transistor (T12), wherein said DC detector (DC-det) is connected to said collector of said second current mirror transistor (T11).
4. Detection circuit according to claim 3, further comprising a RF isolation
25 means (L) connected between the first and second current mirror transistor (T11, T12).
5. Detection circuit according to claim 3 or 4, wherein the detection circuit is implemented on the same chip.